

isc Silicon NPN Power Transistor

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO} = 60V(Min)
- · High DC Current Gain
- · Low Saturation Voltage
- Complement to Type BD828
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

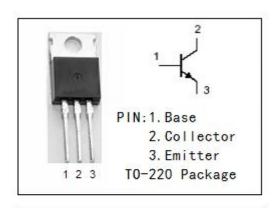
 Designed for driver-stages in hi-fi amplifiers and television circuits.

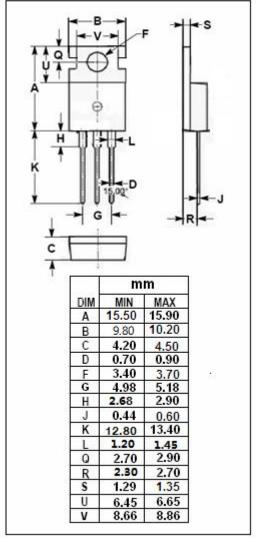
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|---------|------------|--|
| V _{CBO} | Collector-Base Voltage | 60 | V | |
| V _{CEO} | Collector-Emitter Voltage | 60 | V | |
| V _{EBO} | Emitter-Base Voltage | 5 | V | |
| Ic | Collector Current-Continuous | 1.0 | Α | |
| I _{CP} | Collector Current-Peak | 1.5 | Α | |
| Pc | Collector Power Dissipation @ T _a =25°C | 2 | W | |
| | Collector Power Dissipation @ T _C =25°C | 10 | | |
| TJ | Junction Temperature | | $^{\circ}$ | |
| T _{stg} | Storage Temperature Range | -65~150 | $^{\circ}$ | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|---|------|------|
| R _{th j-c} | Thermal Resistance,Junction to Case | 12.5 | °C/W |
| R _{th j-a} | Thermal Resistance, Junction to Ambient | | °C/W |







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BD827

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-Emitter Breakdown Voltage | I _C = 30mA; I _B = 0 | 60 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 500mA; I _B = 50mA | | | 0.5 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = 0.5A ; V _{CE} = 2V | | | 1.0 | V |
| І _{сво} | Collector Cutoff Current | V _{CB} = 30V; I _E = 0 | | | 0.1 | - uA |
| | | V _{CB} = 30V; I _E = 0; T _C = 125°C | | | 10 | |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 10 | uA |
| h _{FE-1} | DC Current Gain | I _C = 5mA ; V _{CE} = 2V | 25 | | | |
| h _{FE-2} | DC Current Gain | I _C = 150mA ; V _{CE} = 2V | 40 | | 250 | |
| h _{FE-3} | DC Current Gain | I _C = 500mA ; V _{CE} = 2V | 25 | | | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = 50mA ; V _{CE} = 5V | | 250 | | MHz |

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